

Amendments to the Specification:

Please replace the paragraph beginning on page 3, line 16, with the following amended paragraph:

The layer thickness of the dielectric layer d_{medium} having the dielectric constant ϵ_{medium} should preferably be selected such that

$$\frac{\epsilon_{\text{medium}} \cdot d_{\epsilon}}{\epsilon \cdot d_{\text{medium}}} > 5$$

so that the metallization structure that is next in the vertical direction is well decoupled. In respect of the decoupling in the horizontal direction, the following should apply

$$\frac{\epsilon_{\text{medium}} \cdot d_{\text{min}}}{d_{\text{medium}} \cdot \epsilon} > 7$$

where d_{min} is the minimum distance to the next metallization structure in the plane.

Please replace the paragraph beginning on page 5, line 4, with the following amended paragraph:

Fig. 3 shows the three-dimensional (i.e., X, Y, Z directions) design of the series resonant circuit structure 20 with the capacitor electrode 22, the line 24, and supply lines 26. As shown in Fig. 3, the capacitor electrode 22 and the ~~The~~ supply lines 26 connect to the line 24.